

Signetics

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Status	Product Specification
FAST Products	

FAST 74F189A

64-Bit TTL Bipolar RAM, Inverting (3-State)

FEATURES

- High speed performance
- Replaces 74F189
- Address access time: 8 ns max vs 28ns for 74F189
- Power dissipation: 4.3 mW/bit typ
- Schottky clamped TTL
- One chip enable
- Inverting outputs (For non-inverting outputs see 74F219A)
- Buffered PNP inputs
- 3-state outputs
- 74F189A in 150 mil wide S.O. is preferred option for new designs
- C3F189A in 300 mil wide S.O.L. replaces 74F189 in existing designs

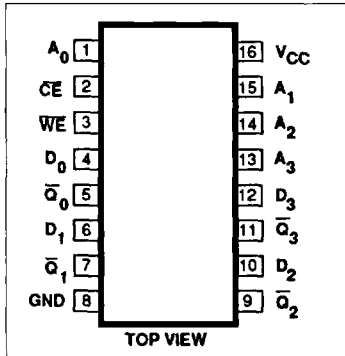
APPLICATIONS

- Scratch pad memory
- Buffer memory
- Push down stacks
- Control store

DESCRIPTION

The 74F189A is a high speed, 64-Bit RAM organized as a 16-word by 4-bit array. Address inputs are buffered to

PIN CONFIGURATION



TYPE	TYPICAL ACCESS TIME	TYPICAL SUPPLY CURRENT (TOTAL)
74F189A	5ns	55mA

ORDERING INFORMATION

PACKAGES	COMMERCIAL RANGE $V_{CC} = 5V \pm 10\%$; $T_A = 0^\circ C$ to $+70^\circ C$
16-Pin Plastic DIP	N74F189AN
16-Pin Plastic SO (150 mil)	N74F189AD
16-Pin Plastic SOL (300 mil)	C3F189AD

INPUT AND OUTPUT LOADING AND FAN-OUT TABLE

PINS	DESCRIPTION	74F(U.L.) HIGH/LOW	LOAD VALUE HIGH/LOW
$D_0 - D_3$	Data inputs	1.0/1.0	20 μ A/0.6mA
$A_0 - A_3$	Address inputs	1.0/1.0	20 μ A/0.6mA
\overline{CE}	Chip Enable input (active Low)	1.0/2.0	20 μ A/1.2mA
\overline{WE}	Write Enable input (active Low)	1.0/2.0	20 μ A/1.2mA
$\overline{Q}_0 - \overline{Q}_3$	Data outputs	150/40	3.0mA/24mA

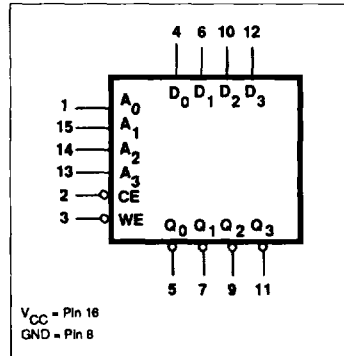
NOTE:

One (1.0) FAST Unit Load is defined as: 20 μ A in the High state and 0.6mA in the Low state.

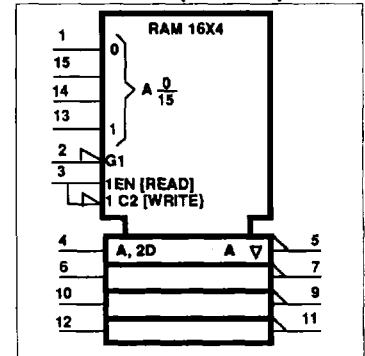
minimize loading and are fully decoded on-chip. The outputs are in High impedance state whenever the Chip Enable

(\overline{CE}) is High. The outputs are active only in the READ mode ($\overline{WE} =$ High) and the output data is the complement of the stored data.

LOGIC SYMBOL



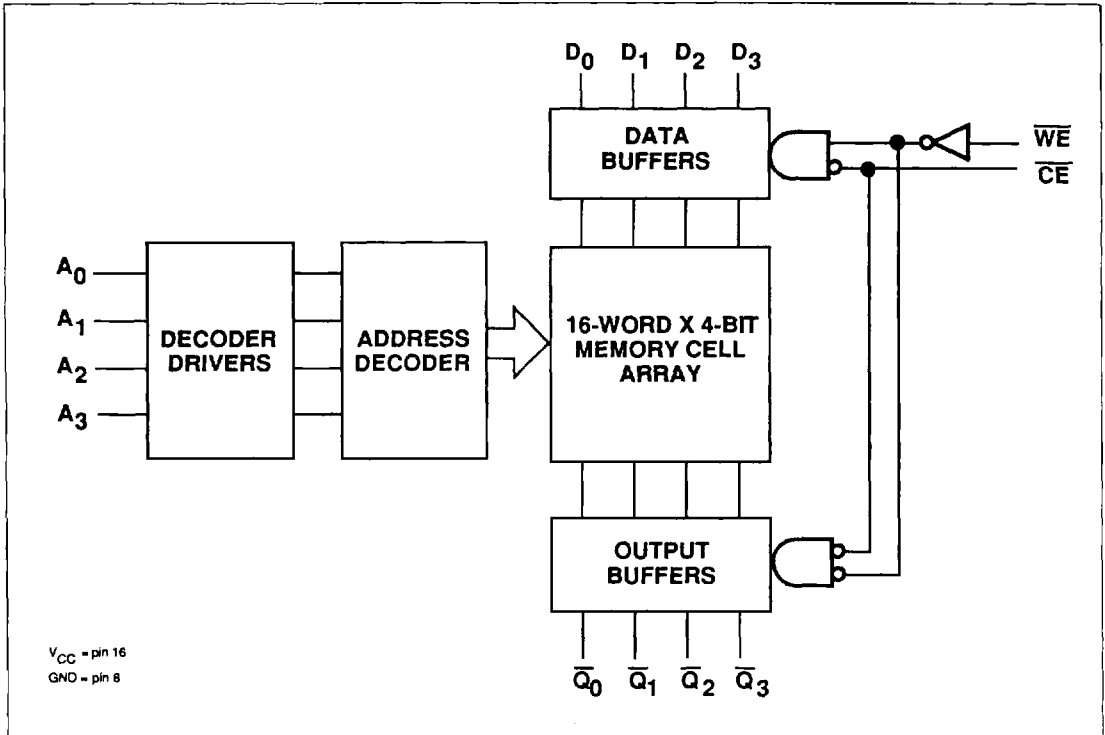
LOGIC SYMBOL (IEEE/IEC)



64-Bit TTL Bipolar RAM (16X4)

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LOGIC DIAGRAM



FUNCTION TABLE

INPUTS			OUTPUT	OPERATING MODE
\overline{CE}	\overline{WE}	D_n	\overline{Q}_n	
L	H	X	Complement of stored data	Read
L	L	L	High impedance	Write "0"
L	L	H	High impedance	Write "1"
H	X	X	High impedance	Disable Input

H = High voltage level
L = Low voltage level
X = Don't care

ABSOLUTE MAXIMUM RATINGS (Operation beyond the limits set forth in this table may impair the useful life of the device. Unless otherwise noted these limits are over the operating free-air temperature range.)

SYMBOL	PARAMETER	RATING	UNIT
V_{CC}	Supply voltage	-0.5 to +7.0	V
V_{IN}	Input voltage	-0.5 to +7.0	V
I_{IN}	Input current	-30 to +5	mA
V_{OUT}	Voltage applied to output in High output state	-0.5 to + V_{CC}	V
I_{OUT}	Current applied to output in Low output state	48	mA
T_A	Operating free-air temperature range	0 to +70	°C
T_{STG}	Storage temperature	-65 to +150	°C

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RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	LIMITS			UNIT
		Min	Nom	Max	
V_{CC}	Supply voltage	4.5	5.0	5.5	V
V_{IH}	High-level input voltage	2.0			V
V_{IL}	Low-level input voltage			0.8	V
I_{IK}	Input clamp current			-18	mA
I_{OH}	High-level output current			-3	mA
I_{OL}	Low-level output current			24	mA
T_A	Operating free-air temperature range	0		70	°C

DC ELECTRICAL CHARACTERISTICS (Over recommended operating free-air temperature range unless otherwise noted.)

SYMBOL	PARAMETER	TEST CONDITIONS ¹	LIMITS			UNIT	
			Min	Typ ²	Max		
V_{OH}	High-level output voltage	$V_{CC} = \text{MIN}, V_{IL} = \text{MAX}$	$\pm 10\%V_{CC}$	2.4		V	
		$V_{IH} = \text{MIN}, I_{OH} = \text{MAX}$	$\pm 5\%V_{CC}$	2.7	3.4	V	
V_{OL}	Low-level output voltage	$V_{CC} = \text{MIN}, V_{IL} = \text{MAX}$	$\pm 10\%V_{CC}$		0.35	0.50	V
		$V_{IH} = \text{MIN}, I_{OL} = \text{MAX}$	$\pm 5\%V_{CC}$		0.35	0.50	V
V_{IK}	Input clamp voltage	$V_{CC} = \text{MIN}, I_I = I_{IK}$		-0.73	-1.2	V	
I_I	Input current at maximum input voltage	$V_{CC} = \text{MAX}, V_I = 7.0\text{V}$			100	μA	
I_{IH}	High-level input current	$V_{CC} = \text{MAX}, V_I = 2.7\text{V}$			20	μA	
I_{IL}	Low-level input current	Others $\overline{CE}, \overline{WE}$	$V_{CC} = \text{MAX}, V_I = 0.5\text{V}$			-0.6	mA
							-1.2
I_{OZH}	Off-state output current High-level voltage applied	$V_{CC} = \text{MAX}, V_O = 2.7\text{V}$			50	mA	
I_{OZL}	Off-state output current Low-level voltage applied	$V_{CC} = \text{MAX}, V_O = 0.5\text{V}$			-50	mA	
I_{OS}	Short-circuit output current ³	$V_{CC} = \text{MAX}$		-60	-150	mA	
I_{CC}	Supply current (total)	$V_{CC} = \text{MAX}, \overline{CE} = \overline{WE} = \text{GND}$		55	80	mA	
C_{IN}	Input capacitance	$V_{CC} = 5\text{V}, V_{IN} = 2.0\text{V}$		4		pF	
C_{OUT}	Output capacitance	$V_{CC} = 5\text{V}, V_{OUT} = 2.0\text{V}$		7		pF	

NOTES:

- For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions for the applicable type.
- All typical values are at $V_{CC} = 5\text{V}, T_A = 25^\circ\text{C}$.
- Not more than one output should be shorted at a time. For testing I_{OS} , the use of high-speed test apparatus and/or sample-and-hold techniques are preferable in order to minimize internal heating and more accurately reflect operational values. Otherwise, prolonged shorting of a High output may raise the chip temperature well above normal and thereby cause invalid readings in other parameter tests. In any sequence of parameter tests, I_{OS} tests should be performed last.

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AC ELECTRICAL CHARACTERISTICS

SYMBOL	PARAMETER		TEST CONDITION	LIMITS					UNIT
				T _A = +25°C V _{CC} = 5V C _L = 50pF R _L = 500Ω			T _A = 0°C to +70°C V _{CC} = 5V ±10% C _L = 50pF R _L = 500Ω		
				Min	Typ	Max	Min	Max	
t _{PLH} t _{PHL}	Access time	Propagation delay A _n to \overline{Q}_n	Waveform 1	2.5 2.0	5.0 4.5	8.0 8.0	2.5 2.0	8.0 8.0	ns
t _{PZH} t _{PZL}		Enable time \overline{CE} to \overline{Q}_n	Waveform 2	2.0 2.0	3.5 4.0	6.0 7.0	1.5 2.0	7.0 7.5	ns
t _{PHZ} t _{PLZ}	Disable time \overline{CE} to \overline{Q}_n		Waveform 3	2.5 1.5	4.5 3.0	7.0 5.5	2.0 1.5	8.0 6.0	ns
t _{PZH} t _{PZL}	Write Recovery time	Enable time \overline{WE} to \overline{Q}_n	Waveform 4	2.0 2.5	4.0 4.5	6.5 7.5	2.0 2.5	7.0 8.0	ns
t _{PHZ} t _{PLZ}	Disable time \overline{WE} to \overline{Q}_n		Waveform 4	3.5 1.5	5.5 3.5	8.5 6.5	3.0 1.5	9.0 7.0	ns

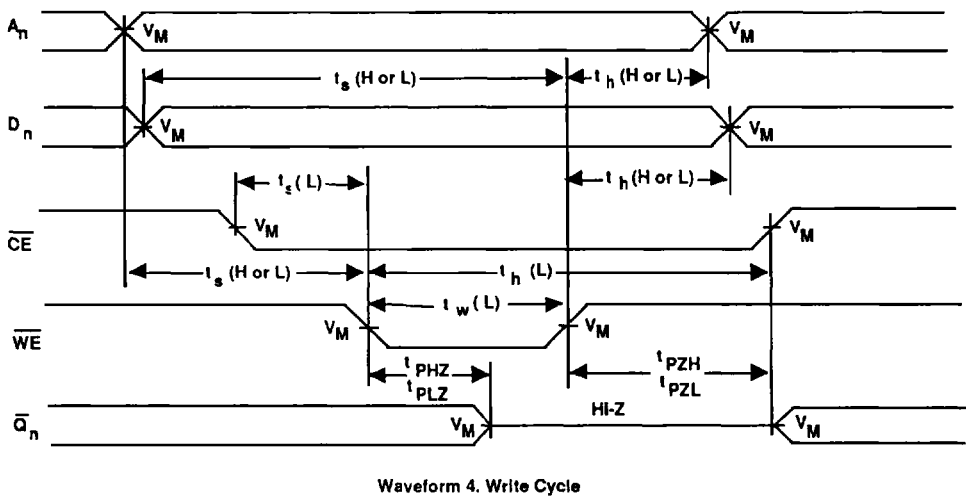
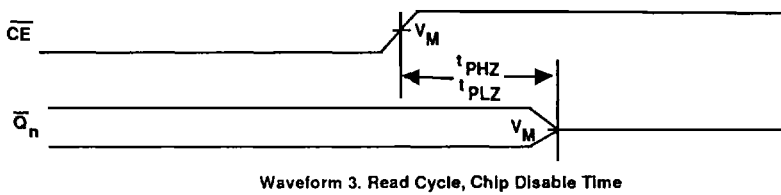
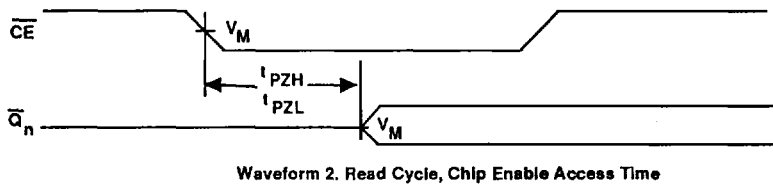
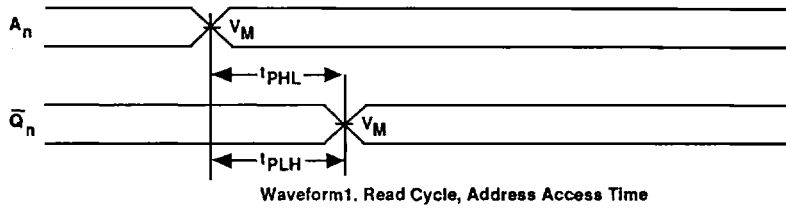
AC SETUP REQUIREMENTS

SYMBOL	PARAMETER		TEST CONDITION	LIMITS					UNIT
				T _A = +25°C V _{CC} = 5V C _L = 50pF R _L = 500Ω			T _A = 0°C to +70°C V _{CC} = 5V ±10% C _L = 50pF R _L = 500Ω		
				Min	Typ	Max	Min	Max	
t _s (H) t _s (L)	Setup time A _n to \overline{WE}		Waveform 4	4.5 4.5			5.0 5.0		ns
t _h (H) t _h (L)	Hold time A _n to \overline{WE}		Waveform 4	0 0			0 0		ns
t _s (H) t _s (L)	Setup time D _n to \overline{WE}		Waveform 4	7.5 6.5			9.0 8.0		ns
t _h (H) t _h (L)	Hold time D _n to \overline{WE}		Waveform 4	0 0			0 0		ns
t _s (L)	Setup time \overline{CE} (falling edge) to \overline{WE} (falling edge)		Waveform 4	0			0		ns
t _h (L)	Hold time \overline{WE} (falling edge) to \overline{CE} (rising edge)		Waveform 4	6.5			7.5		ns
t _w (L)	Pulse width, Low \overline{WE}		Waveform 4	7.0			8.0		ns

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AC WAVEFORMS

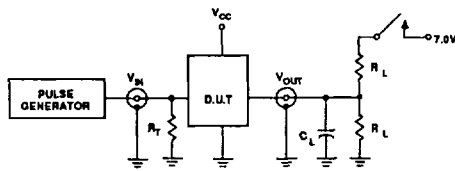


NOTES: 1. For all waveforms, $V_M = 1.5V$.

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TEST CIRCUIT AND WAVEFORMS



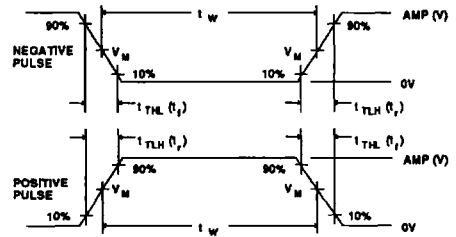
Test Circuit For 3-State Outputs

SWITCH POSITION

TEST	SWITCH
t_{PLZ}	closed
t_{PZL}	closed
All other	open

DEFINITIONS

- R_L = Load resistor; see AC CHARACTERISTICS for value.
- C_L = Load capacitance includes jig and probe capacitance; see AC CHARACTERISTICS for value.
- R_T = Termination resistance should be equal to Z_{OUT} of pulse generators.



$V_M = 1.5V$
Input Pulse Definition

FAMILY	INPUT PULSE REQUIREMENTS				
	Amplitude	Rep. Rate	t_W	t_{TLH}	t_{THL}
74F	3.0V	1MHz	500ns	2.5ns	2.5ns